

IN THE SPECIFICATION

Please replace the paragraph on page 5 lines 25-31, corresponding to paragraph [0020], with the following amended paragraph:

A method of manufacturing a thin film transistor array panel is provided, which includes: forming a gate wire and a storage electrode wire; depositing a gate insulating layer, an amorphous silicon layer, a contact layer, and a metal conductive layer; patterning the ~~metal~~ amorphous silicon layer, the contact layer, and the metal conductive layer to form a data wire, a direction control electrode, and a channel portion of a thin film transistor; forming a passivation layer on the channel portion; and forming a pixel electrode and a connecting portion on the passivation layer.

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